

Seongjun Kim

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11202687/publications.pdf>

Version: 2024-02-01

9
papers

149
citations

1478505

6
h-index

1474206

9
g-index

9
all docs

9
docs citations

9
times ranked

307
citing authors

#	ARTICLE	IF	CITATIONS
1	Temperature-dependent DC characteristics of AlInN/GaN high-electron-mobility transistors. <i>Electronic Materials Letters</i> , 2017, 13, 302-306.	2.2	2
2	Graphene-GaN Schottky diodes. <i>Nano Research</i> , 2015, 8, 1327-1338.	10.4	57
3	Compound Ag nanocluster-graphene electrodes as transparent and current spreading electrodes for improved light output power in near-ultraviolet light emitting diodes. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 215103.	2.8	14
4	Carrier transport mechanism of Mo contact to amorphous hafnium indium zinc oxides. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 1818-1821.	1.8	1
5	Impact of Interlayer Processing Conditions on the Performance of GaN Light-Emitting Diode with Specific NiO _x /Graphene Electrode. <i>ACS Applied Materials & Interfaces</i> , 2013, 5, 958-964.	8.0	37
6	Carrier transport mechanism of low resistance Ti/Al/Au ohmic contacts to AlInN/GaN heterostructures. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	13
7	Effects of Temperature on Current Crowding of GaN-Based Light-Emitting Diodes. <i>IEEE Electron Device Letters</i> , 2013, 34, 277-279.	3.9	9
8	Electrical Characteristics of Pt Schottky Contacts on AlInN:Mg/GaN Heterostructures. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 10MA05.	1.5	2
9	Carrier transport mechanism at metal/amorphous gallium indium zinc oxides interfaces. <i>Applied Physics Letters</i> , 2012, 101, .	3.3	14